

Type No.	V _{CEO} (SUS)	I _c (A)	h _{FE} (MIN.)			SW TIME(MAX.)			Circuit Symbol	Package Style
	V _{CEX} (SUS)# (V)		V _{CE} (V)	I _c (A)	ton (μ)	tstg (μ)	tf (μ)			
MG300M1UK2	1000#	±300	80	5	300	2	15	5	UK	21
MG10Q6EK1	1200#	±10×6	100	5	10	2	14	6	EK	27
MG20Q6EK1	1200#	±20×6	100	5	20	2	14	6	EK	27
MG50Q2YK1	1200#	±50×2	100	5	50	2	13	4	YK	19
MG75Q2YK1	1200#	±75×2	100	5	75	2	12	5	YK	26
MG100Q2YK1	1200#	±100×2	100	5	100	2	13	4	YK	22
MG150Q2YK1	1200#	±150×2	100	5	150	2	12	5	YK	22
MG200Q1UK1	1200#	±200	100	5	200	2	13	4	UK	21
MG300Q1UK1	1200#	±300	100	5	300	2	12	5	UK	21
MG40S2YK1	1400#	±40×2	100	5	40	2	17	3	YK	26
MG80S2YK1	1400#	±80×2	100	5	80	2	17	3	YK	22
MG160S1UK1	1400#	±160	100	5	160	2	17	3	UK	21

b) MOS FET TYPE

Type No.	V _{DSS}	I _D (A)	RDS(ON) (Ω)		SW TIME (MAX.)			Circuit Symbol	Package Style (Refer to page42)
	(V)		I _D (A)	(MAX)	ton (μs)	toff (μs)	tf (μs)		
2SK568	450	±8	8	0.75	0.5	1.0	0.25	AM	1
2SK1513	500	±8	8	0.75	1.0	0.7	0.25	AM	1
2SK1029	500	±10	10	0.50	0.9	0.8	0.2	AM	1
2SK578	150	±15	15	0.22	0.5	0.6	0.2	AM	1
2SK447	250	±15	15	0.24	0.7	1.0	0.4	AM	1
2SK1333	500	±15	15	0.40	1.0	0.7	0.25	AM	1
MG8G4GM1	450	±8×4	8	0.75	0.5	1.0	0.25	GM	15
MG8G6EM1	450	±8×6	8	0.75	0.5	1.0	0.25	EM	16
MG8H6EM1	500	±8×6	8	0.75	1.0	0.7	0.25	EM	16
MG10H4GM1	500	±10×4	10	0.50	0.7	0.8	0.2	GM	15
MG10H6EM1	500	±10×6	10	0.50	0.7	0.8	0.2	EM	16
MG15C4HM1	150	±15×4	15	0.22	0.5	0.6	0.2	HM	18
MG15D4GM1	250	±15×4	15	0.24	0.7	1.0	0.4	GM	15
MG15D4HM1	250	±15×4	15	0.24	0.7	1.0	0.4	HM	18
MG15D6EM1	250	±15×6	15	0.24	0.7	1.0	0.4	EM	16
MG15G1AM1	450	±15	15	0.40	0.6	2.0	0.5	AM	2
MG15G4GM1	450	±15×4	15	0.40	0.6	2.0	0.5	GM	15
MG15G6EM1	450	±15×6	15	0.40	0.6	2.0	0.5	EM	16
MG15H4GM1	500	±15×4	15	0.40	1.0	0.7	0.25	GM	15
MG15H6EM1	500	±15×6	15	0.40	1.0	0.7	0.25	EM	16